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March 2013



## FDB8443 N-Channel PowerTrench<sup>®</sup> MOSFET

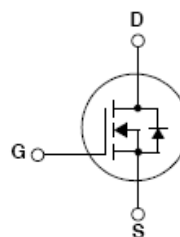
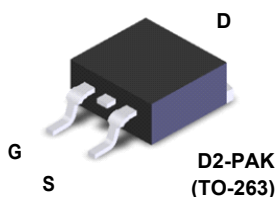
40 V, 182 A, 3.0 mΩ

### Features

- $R_{DS(on)}$  = 2.3 mΩ (Typ.) @  $V_{GS} = 10\text{ V}$ ,  $I_D = 80\text{ A}$
- $Q_{G(tot)}$  = 142 nC (Typ.)
- Low Miller Charge,  $Q_{GD} = 32\text{ nC}$  (Typ.)
- UIS Capability (Single Pulse and Repetitive Pulse)
- RoHS Compliant

### Applications

- Power Tools
- Motor drives and Uninterruptible Power Supplies
- Synchronous Rectification
- Battery Protection Circuit



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDB8443	Unit
$V_{DSS}$	Drain to Source Voltage	40	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ , Silicon Limited)	182*
		- Continuous ( $T_C = 100^\circ\text{C}$ , Silicon Limited)	129*
		- Continuous ( $T_C = 25^\circ\text{C}$ , Package Limited)	120
		- Continuous ( $T_A = 25^\circ\text{C}$ , $R_{\theta JA} = 43^\circ\text{C/W}$ )	25
$I_{DM}$	Drain Current	- Pulsed	See Figure 4
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	531	mJ
$P_D$	Power Dissipation	188	W
	Derate above $25^\circ\text{C}$	1.25	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

\*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

### Thermal Characteristics

Symbol	Parameter	FDB8443	Unit
$R_{\theta JC}$	Thermal Resistance Junction to Case, Max.	0.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, Max. (Note 2)	62	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-263, 1in <sup>2</sup> copper pad area, Max.	43	$^\circ\text{C/W}$

FDB8443 N-Channel PowerTrench<sup>®</sup> MOSFET

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB8443	FDB8443	TO-263AB	330mm	24mm	800 units

### Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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#### Off Characteristics

$B_{VDSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}$ $T_C = 150^\circ\text{C}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

#### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	2.8	4	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}, V_{GS} = 10\text{V}$ $I_D = 80\text{A}, V_{GS} = 10\text{V}, T_J = 175^\circ\text{C}$	-	2.3	3.0	$\text{m}\Omega$
			-	4.2	5.5	

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	9310	-	pF
$C_{oss}$	Output Capacitance		-	800	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	510	-	pF
$R_G$	Gate Resistance	$V_{GS} = 0.5\text{V}, f = 1\text{MHz}$	-	0.9	-	$\Omega$
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	-	142	185	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V	-	17.5	23	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DD} = 20\text{V}, I_D = 35\text{A}, I_g = 1\text{mA}$	-	36	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	18.8	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	32	-	nC

#### Switching Characteristics ( $V_{GS} = 10\text{V}$ )

$t_{on}$	Turn-On Time	$V_{DD} = 20\text{V}, I_D = 35\text{A}, V_{GS} = 10\text{V}, R_{GS} = 2\Omega$	-	-	58	ns
$t_{d(on)}$	Turn-On Delay Time		-	18.4	-	ns
$t_r$	Rise Time		-	17.9	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	55	-	ns
$t_f$	Fall Time		-	13.5	-	ns
$t_{off}$	Turn-Off Time		-	-	109	ns

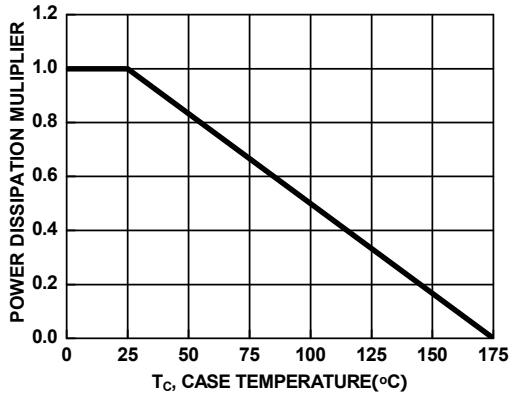
#### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Voltage	$I_{SD} = 35\text{A}$	-	0.8	1.25	V
		$I_{SD} = 15\text{A}$	-	0.8	1.0	
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 35\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	42	55	ns
$Q_{rr}$	Reverse Recovery Charge		-	48	62	nC

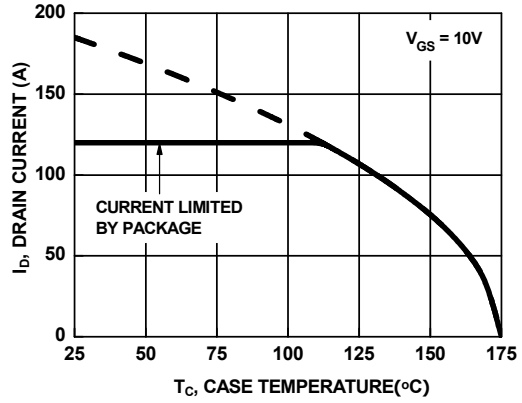
#### Notes:

- Starting  $T_J = 25^\circ\text{C}, L = 0.26\text{mH}, I_{AS} = 64\text{A}$ .
- Pulse width = 100s.

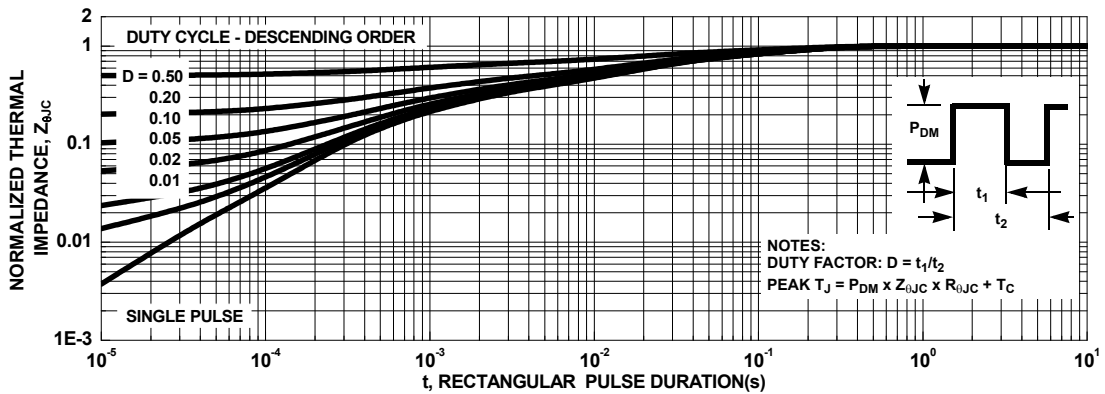
**Typical Characteristics**



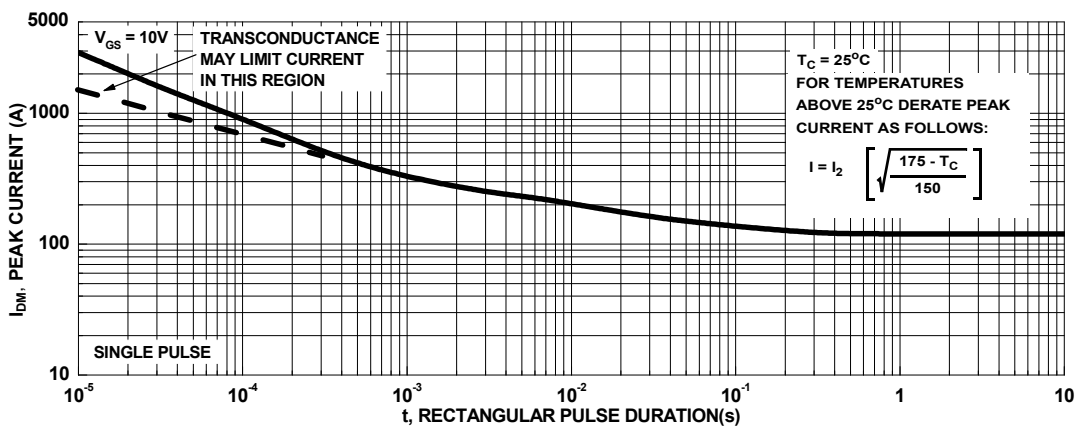
**Figure 1. Normalized Power Dissipation vs Case Temperature**



**Figure 2. Maximum Continuous Drain Current vs Case Temperature**

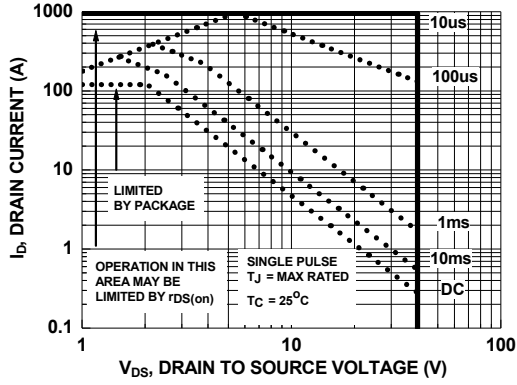


**Figure 3. Normalized Maximum Transient Thermal Impedance**

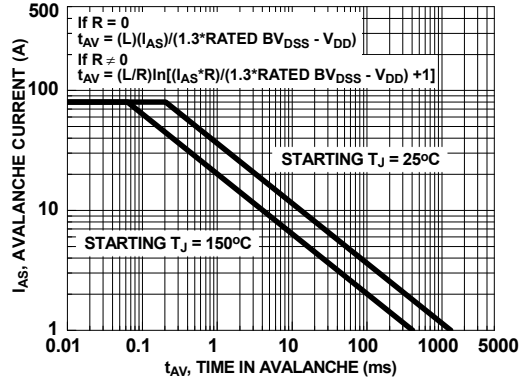


**Figure 4. Peak Current Capability**

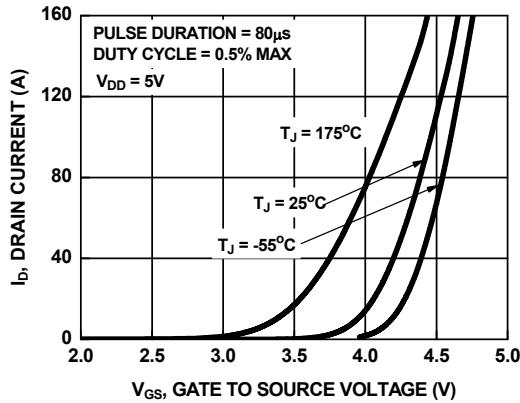
**Typical Characteristics**



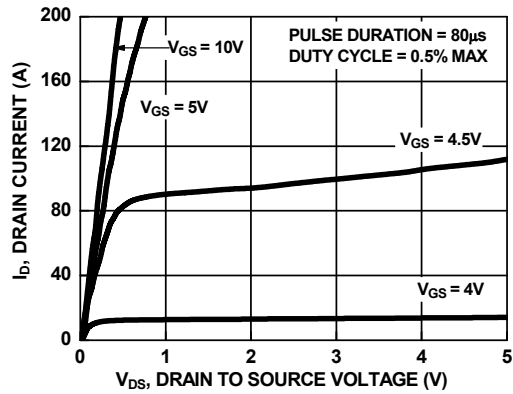
**Figure 5. Forward Bias Safe Operating Area**



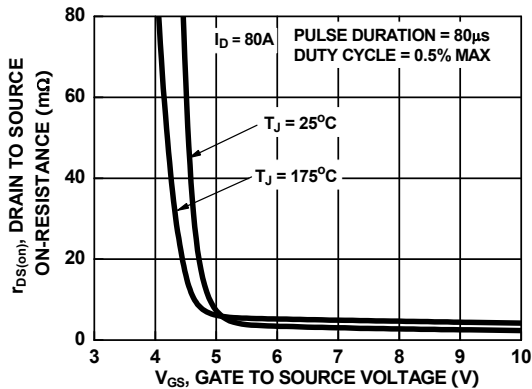
NOTE: Refer to Fairchild Application Notes AN7514 and AN7515  
**Figure 6. Unclamped Inductive Switching Capability**



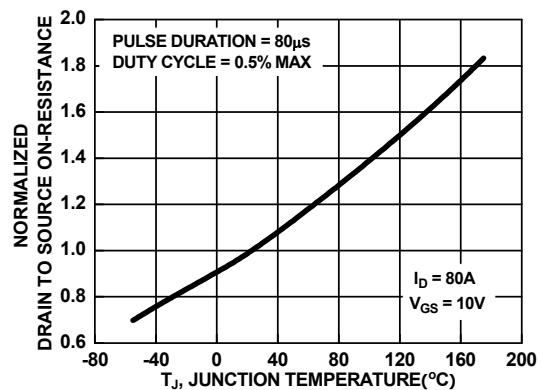
**Figure 7. Transfer Characteristics**



**Figure 8. Saturation Characteristics**



**Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage**



**Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature**

**Typical Characteristics**

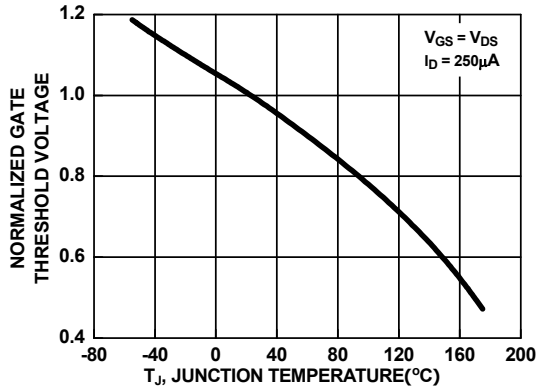


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

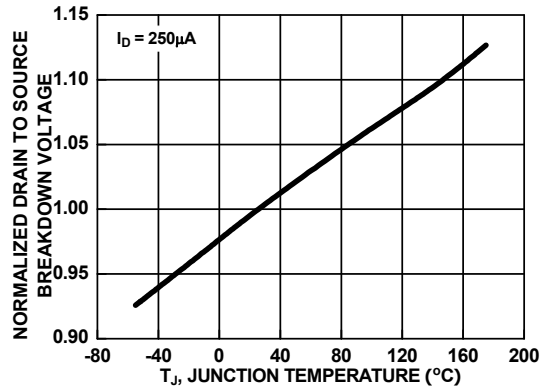


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

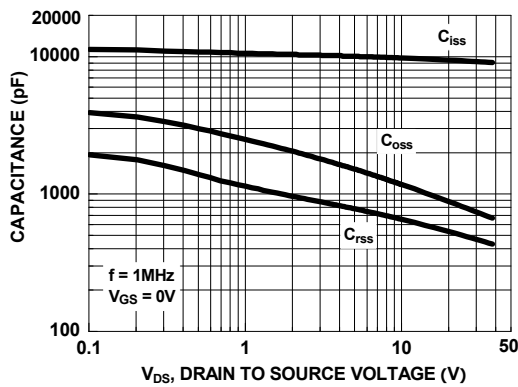


Figure 13. Capacitance vs Drain to Source Voltage

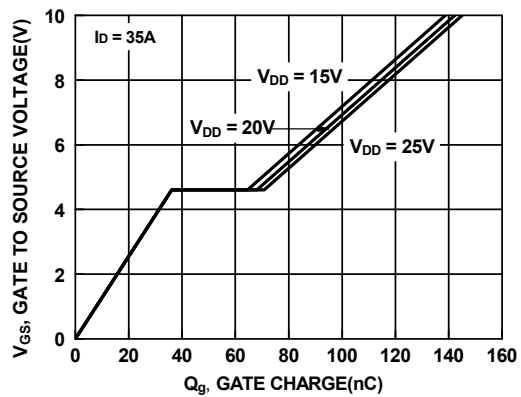


Figure 14. Gate Charge vs Gate to Source Voltage

